



DMNH6042SK3

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
60V	50mΩ @ V _{GS} = 10V	25A
	65mΩ @ V _{GS} = 4.5V	22A

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- Power Management Functions
- DC-DC Converters
- Backlighting

60V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET

Features

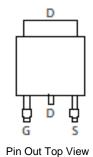
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low On-Resistance
- Low Input Capacitance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (<u>DMNH6042SK3Q</u>)

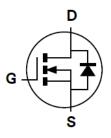
Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 ⁽²⁾
- Weight: 0.315 grams (Approximate)



Top View





Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMNH6042SK3-13	TO252 (DPAK)	2,500/Tape & Reel

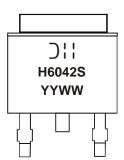
Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



) | | = Manufacturer's Marking H6042S = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 16 = 2016) WW = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	60	V		
Gate-Source Voltage	V _{GSS}	±20	V		
Continuous Drain Current (Note 7) V_{GS} = 10V	Steady State	$T_{C} = +25^{\circ}C$ $T_{C} = +70^{\circ}C$	ID	25 17	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I _{DM}	40	А
Maximum Continuous Body Diode Forward Current (Note 7)			ls	25	A
Avalanche Current (Note 8) L = 10mH			I _{AS}	3.5	A
Avalanche Energy (Note 8) L = 10mH			E _{AS}	65	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 5)		PD	2	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Р	73	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	36	
Total Power Dissipation (Note 6)		PD	3.5	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Devi	43	°C/W
Thermal Resistance, Sunction to Ambient (Note 0)	t<10s	R _{0JA}	21	
Thermal Resistance, Junction to Case (Note 7)	R _{θJC}	3.2		
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current TJ = +25°C	IDSS	—	_	1	μA	$V_{DS} = 60V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	1.0	_	3.0	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
Static Drain-Source On-Resistance			30	50	~0	$V_{GS} = 10V, I_D = 6A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	45	65	mΩ	$V_{GS} = 4.5V, I_D = 6A$	
Diode Forward Voltage	V _{SD}	_	0.8	1.2	V	$V_{GS} = 0V, I_{S} = 2.6A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss		492	_	рF		
Output Capacitance	Coss		54	_	pF	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	Crss		27	_	pF		
Gate Resistance	Rg	—	3.8	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	4.2	—	nC		
Total Gate Charge (V _{GS} = 10V)	Qg	—	8.8	—	nC		
Gate-Source Charge	Q _{gs}	_	1.8	—	nC	$V_{DS} = 44V, I_D = 5.2A$	
Gate-Drain Charge	Q _{gd}	_	1.8	—	nC	7	
Turn-On Delay Time	t _{D(ON)}	_	3.4		ns		
Turn-On Rise Time	t _R	_	1.9	_	ns	$V_{GS} = 10V, V_{DS} = 30V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	10.1		ns	$R_G = 6\Omega, I_D = 1A$	
Turn-Off Fall Time	t _F	_	4.5		ns	7	
Body Diode Reverse Recovery Time	t _{RR}	_	12.9		ns		
Body Diode Reverse Recovery Charge	Q _{RR}	_	5.4	—	nC	−I _F = 2.6A, di/dt = 100A/μs	

Notes:

Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

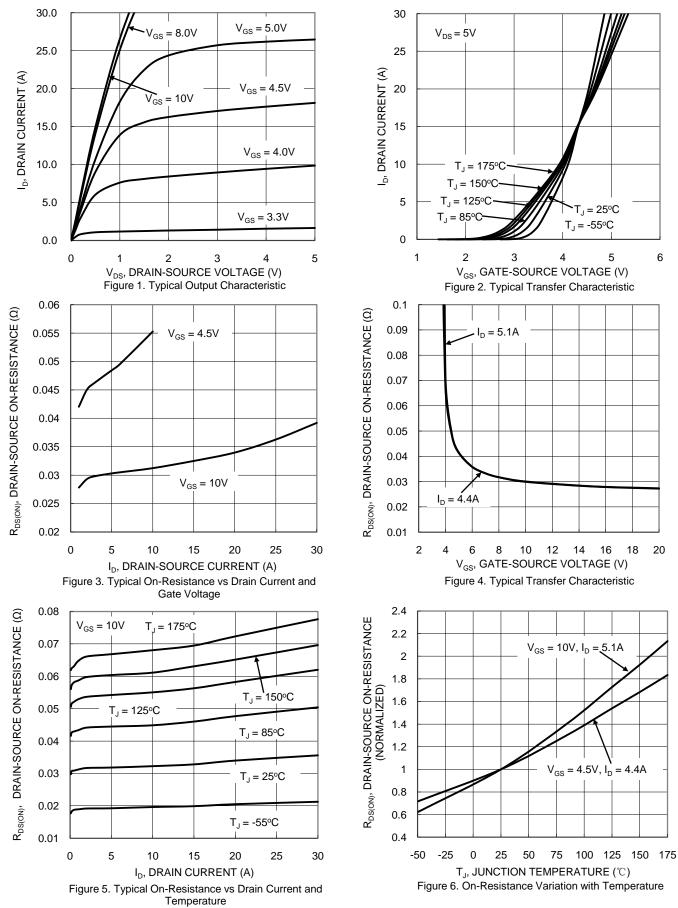
7. Thermal resistance from junction to soldering point (on the exposed drain pad).

8. I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$.

Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.

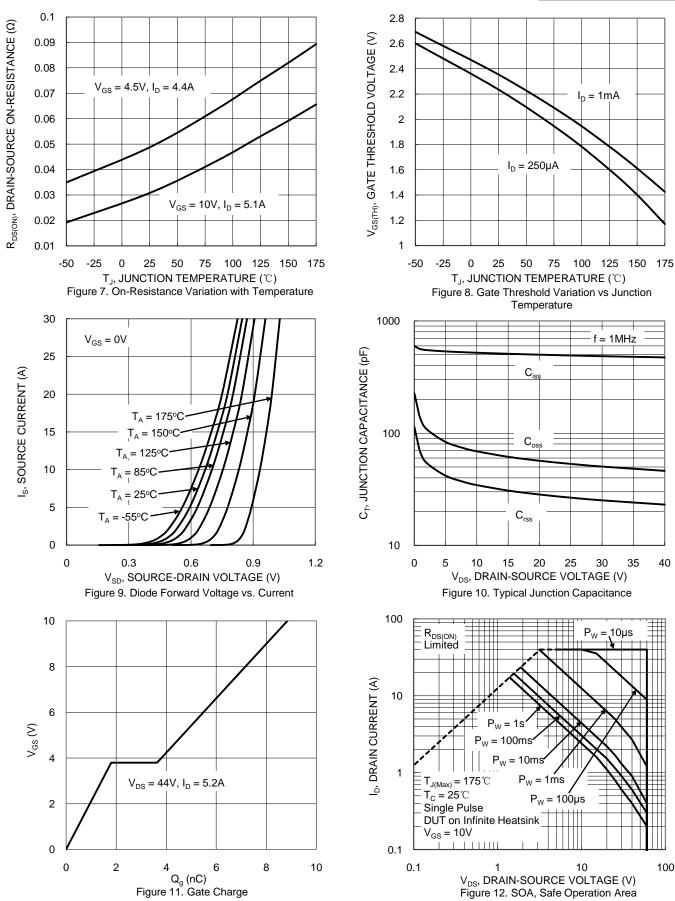


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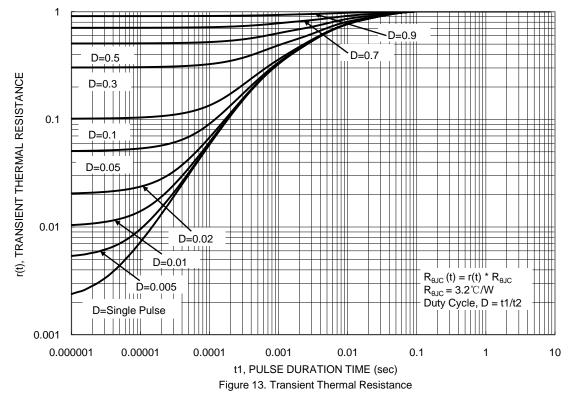




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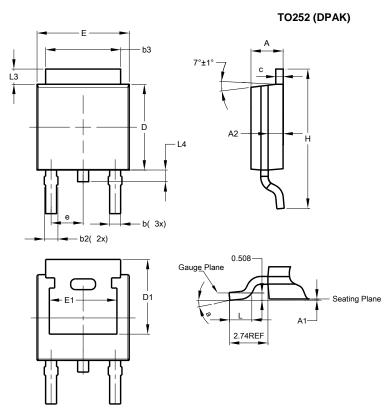






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

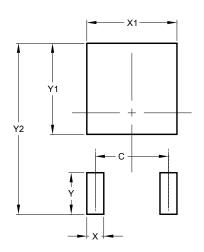


	TO252 (DPAK)						
Dim	Min	Max	Тур				
Α	2.19	2.39	2.29				
A1	0.00	0.13	0.08				
A2	0.97	1.17	1.07				
b	0.64	0.88	0.783				
b2	0.76	1.14	0.95				
b3	5.21	5.46	5.33				
С	0.45	0.58	0.531				
D	6.00	6.20	6.10				
D1	5.21	-	-				
е	-	-	2.286				
Ε	6.45	6.70	6.58				
E1	4.32	-	-				
Н	9.40	10.41	9.91				
L	1.40	1.78	1.59				
L3	0.88	1.27	1.08				
L4	0.64	1.02	0.83				
а	0°	10°	-				
All	All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)			
С	4.572			
Х	1.060			
X1	5.632			
Y	2.600			
Y1	5.700			
Y2	10.700			



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